

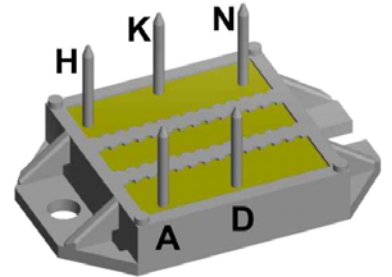
Standard Rectifier Module

3~ Rectifier	
V_{RRM} =	800 V
I_{DAV} =	30 A
I_{FSM} =	120 A

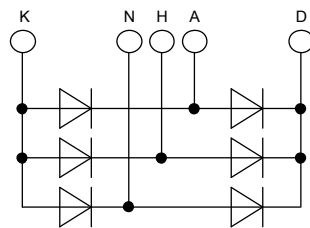
3~ Rectifier Bridge

Part number

VUO28-08NO7



E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

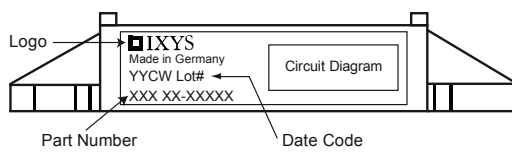
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: ECO-PAC1

- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 9 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V	
I_R	reverse current	$V_R = 800 V$	$T_{VJ} = 25^{\circ}C$		10	μA	
		$V_R = 800 V$	$T_{VJ} = 150^{\circ}C$		0.7	mA	
V_F	forward voltage drop	$I_F = 10 A$	$T_{VJ} = 25^{\circ}C$		1.20	V	
		$I_F = 30 A$			1.61	V	
		$I_F = 10 A$	$T_{VJ} = 125^{\circ}C$		1.14	V	
		$I_F = 30 A$			1.68	V	
I_{DAV}	bridge output current	$T_C = 105^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 150^{\circ}C$		30	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.84	V	
r_F	slope resistance				28.8	m Ω	
R_{thJC}	thermal resistance junction to case				2.5	K/W	
R_{thCH}	thermal resistance case to heatsink			0.4		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		50	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		120	A	
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		130	A	
		$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		100	A	
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		110	A	
I^2t	value for fusing	$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		72	A ² s	
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		70	A ² s	
		$t = 10 \text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		50	A ² s	
		$t = 8,3 \text{ ms; (60 Hz), sine}$	$V_R = 0 V$		50	A ² s	
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		4	pF	

Package ECO-PAC1		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				19		g
M_D	mounting torque		1.5		2	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	10.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO28-08NO7	VUO28-08NO7	Box	25	491772

Equivalent Circuits for Simulation

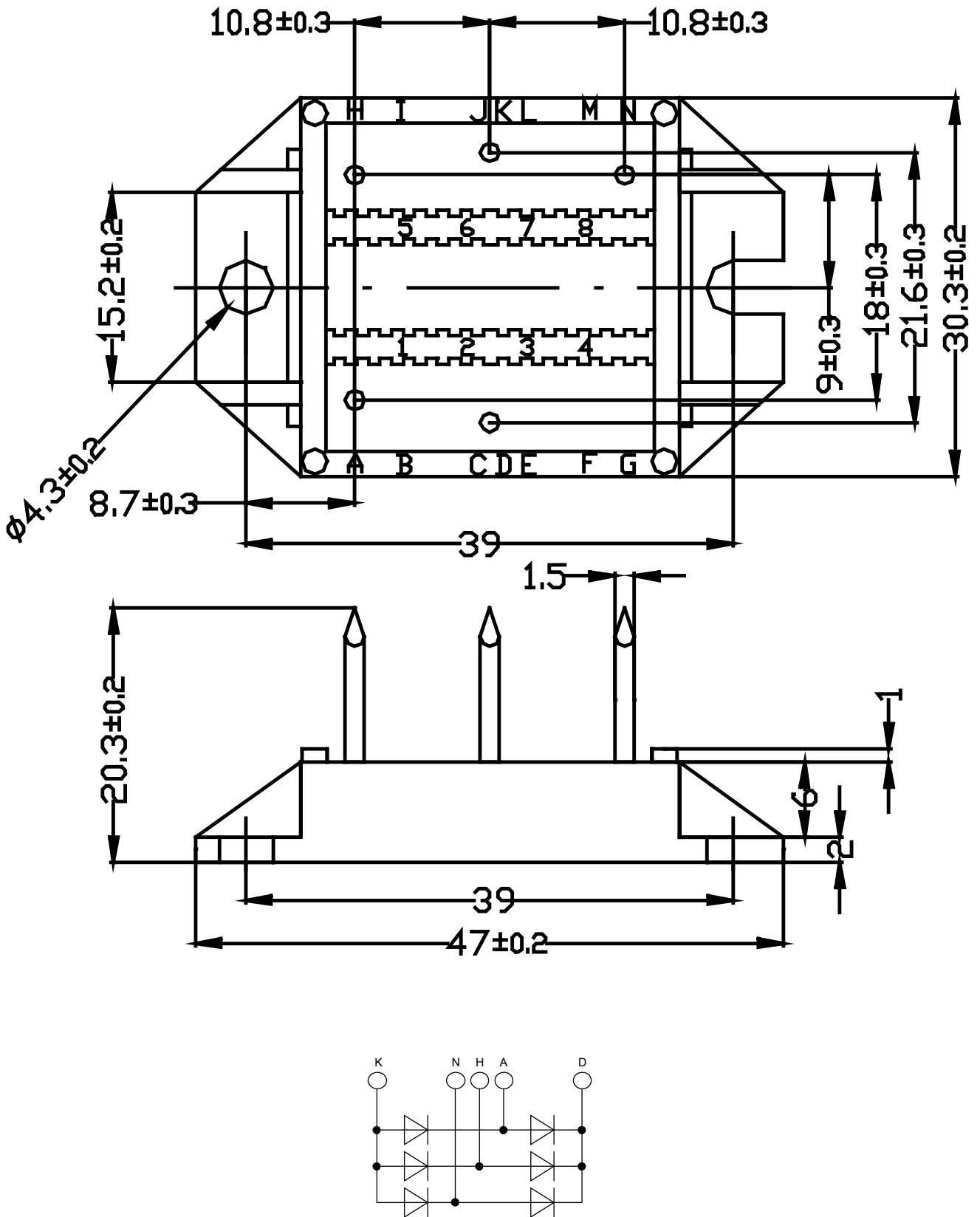
* on die level

$T_{VJ} = 150^\circ\text{C}$



Rectifier

$V_{0\ max}$	threshold voltage	0.84	V
$R_{0\ max}$	slope resistance *	27.6	mΩ



Rectifier

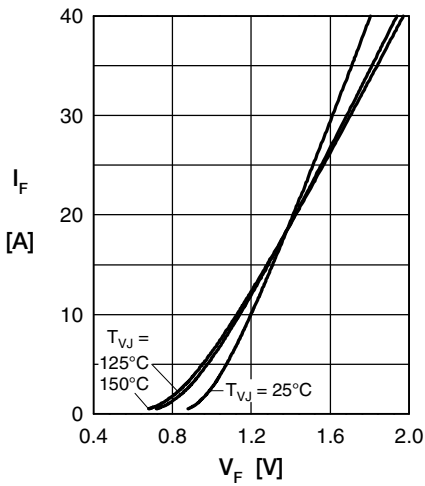


Fig. 1 Forward current vs. voltage drop per diode

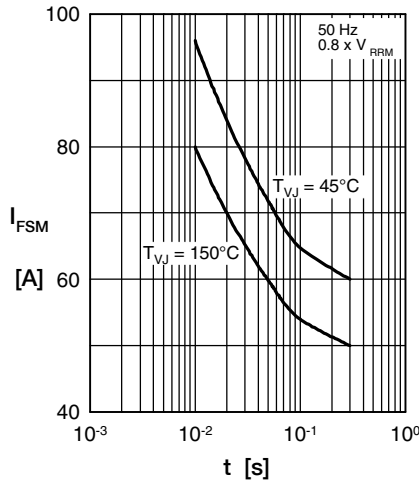


Fig. 2 Surge overload current vs. time per diode

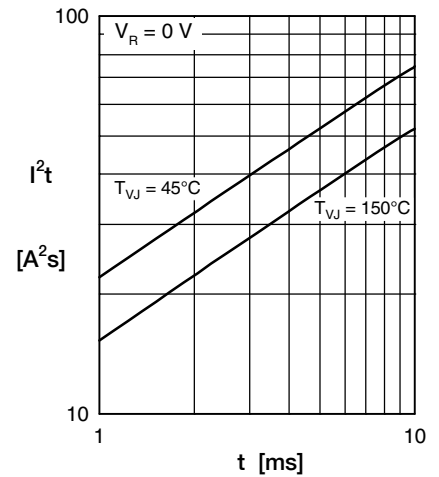


Fig. 3 I²t vs. time per diode

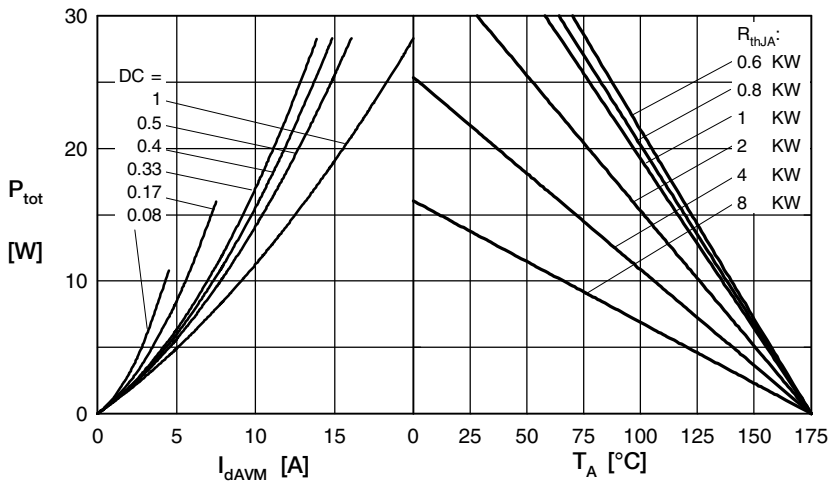


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

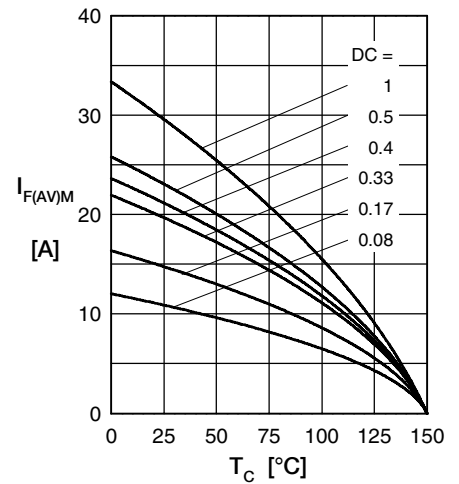


Fig. 5 Max. forward current vs. case temperature per diode

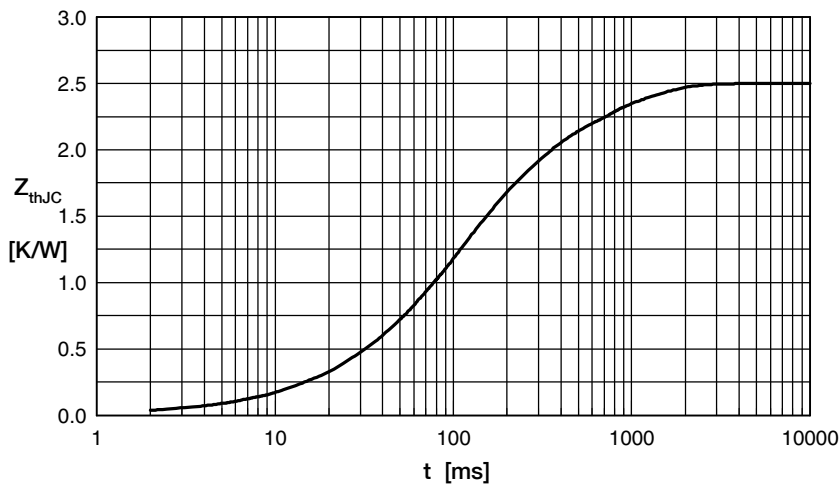


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	1.359	0.1015
2	0.3286	0.1026
3	0.1651	0.4919
4	0.6473	0.62